19 December 2013

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Exposed drain pad for excellent thermal conduction
- Tin-plated 100 % solderable side pads for optical solder inspection
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V
V_{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	4.4	Α
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 3 \text{ A}; T_j = 25 ^{\circ}\text{C}$		-	72	95	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	1 6	D I
2	D	drain	7 5	
3	G	gate		G T
4	S	source	3 8 4	
5	D	drain	Transparent top view	
6	D	drain	DFN2020MD-6 (SOT1220)	S 017aaa255
7	D	drain		
8	S	source		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMPB85ENEA	DFN2020MD-6	DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220

7. Marking

Table 4. Marking codes

Type number	Marking code
PMPB85ENEA	2C

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	4.4	Α
		V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	3	Α
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	1.9	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	12	Α

PMPB85ENEA

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Symbol	Parameter	Conditions		Min	Max	Unit
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = 0.4 A; DUT in avalanche (unclamped)		-	12.6	mJ
P _{tot}	total power dissipation	T _{amb} = 25 °C	[1]	-	1.6	W
		T _{amb} = 25 °C; t ≤ 5 s	[1]	-	3.3	W
		T _{sp} = 25 °C		-	15.6	W
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain o	diode					,
I _S	source current	T _{amb} = 25 °C	[1]	-	1	Α
ESD maximum	rating					*
V _{ESD}	electrostatic discharge voltage	НВМ	[2]	-	2000	V

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Measured between all pins.

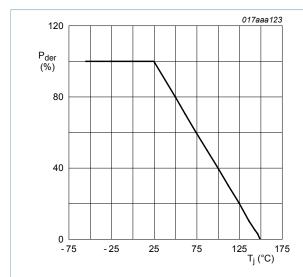


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

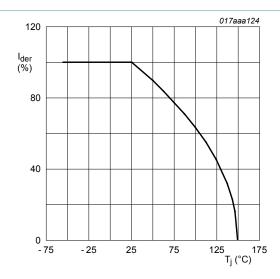


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

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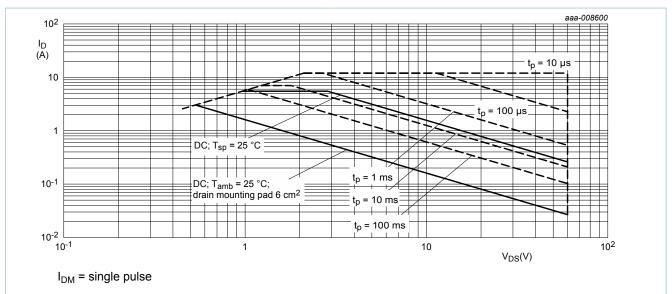


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient		_	[1]	-	239	275	K/W
			<u>[2]</u>	-	68	78	K/W
	ambient	in free air; t ≤ 5 s	<u>[2]</u>	-	33	38	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	4	8	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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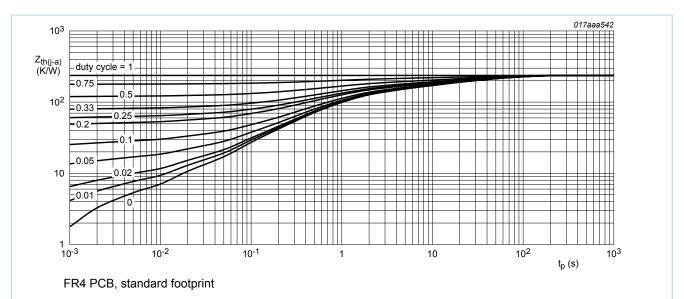


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

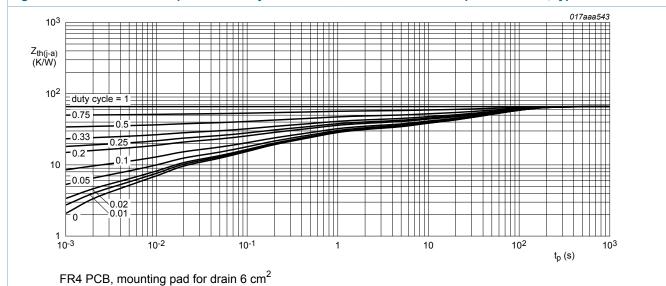


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	1.3	1.7	2.7	V
I _{DSS} drain leaka	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 150 °C	-	-	10	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μA
	V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μA	
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 3 A; T _j = 25 °C	-	72	95	mΩ
res	resistance	V _{GS} = 10 V; I _D = 3 A; T _j = 150 °C	-	135	175	mΩ
		V _{GS} = 4.5 V; I _D = 2.8 A; T _j = 25 °C	-	85	120	mΩ
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 3 A; T_{j} = 25 °C	-	11.5	-	S
R_G	gate resistance	f = 1 MHz; T _j = 25 °C	-	1.7	-	Ω
Dynamic	characteristics			1		
Q _{G(tot)}	total gate charge	$V_{DS} = 30 \text{ V}; I_D = 3 \text{ A}; V_{GS} = 10 \text{ V};$	-	6.2	9.2	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.8	-	nC
Q_{GD}	gate-drain charge		-	1.2	-	nC
C _{iss}	input capacitance	V _{DS} = 30 V; f = 1 MHz; V _{GS} = 0 V;	-	305	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	40	-	pF
C _{rss}	reverse transfer capacitance		-	25	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 30 V; I _D = 3 A; V _{GS} = 10 V;	-	4	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	3.5	-	ns
t _{d(off)}	turn-off delay time		-	10.5	-	ns
t _f	fall time		-	4.5	-	ns
Source-d	rain diode			1	1	
V_{SD}	source-drain voltage	I _S = 1 A; V _{GS} = 0 V; T _j = 25 °C	-	0.8	1.2	V

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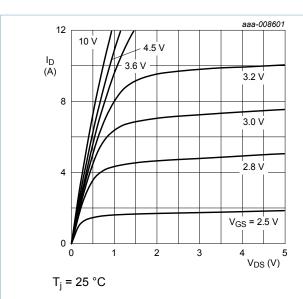


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

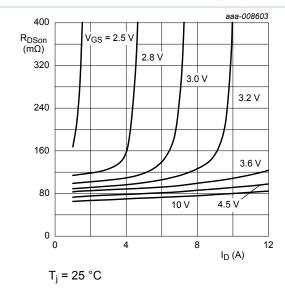


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

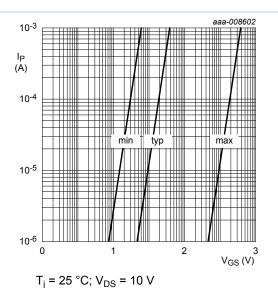


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

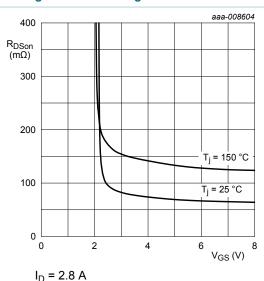


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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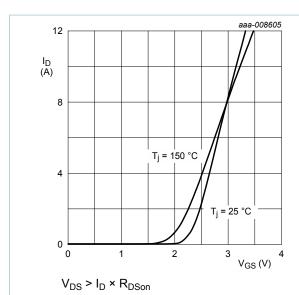


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

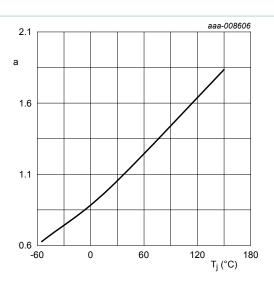


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

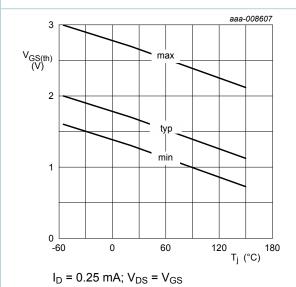
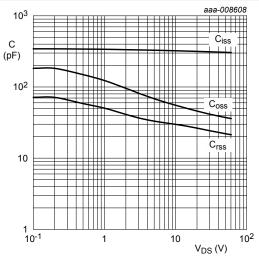


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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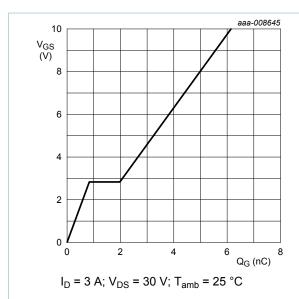


Fig. 14. Gate-source voltage as a function of gate charge; typical values

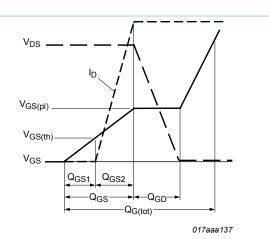


Fig. 15. MOSFET transistor: Gate charge waveform definitions

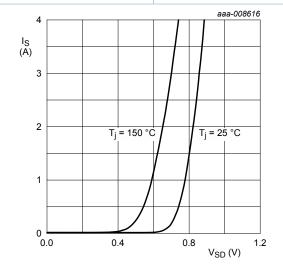
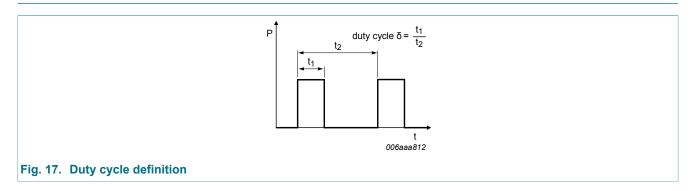


Fig. 16. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$

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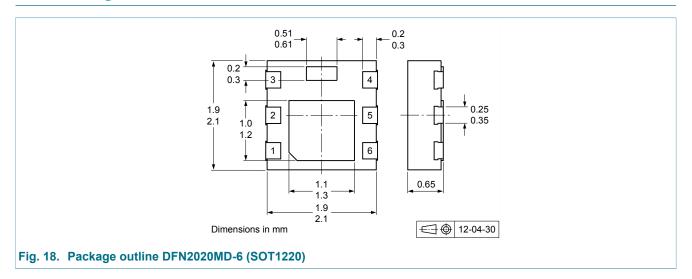
11. Test information



11.1 Quality information

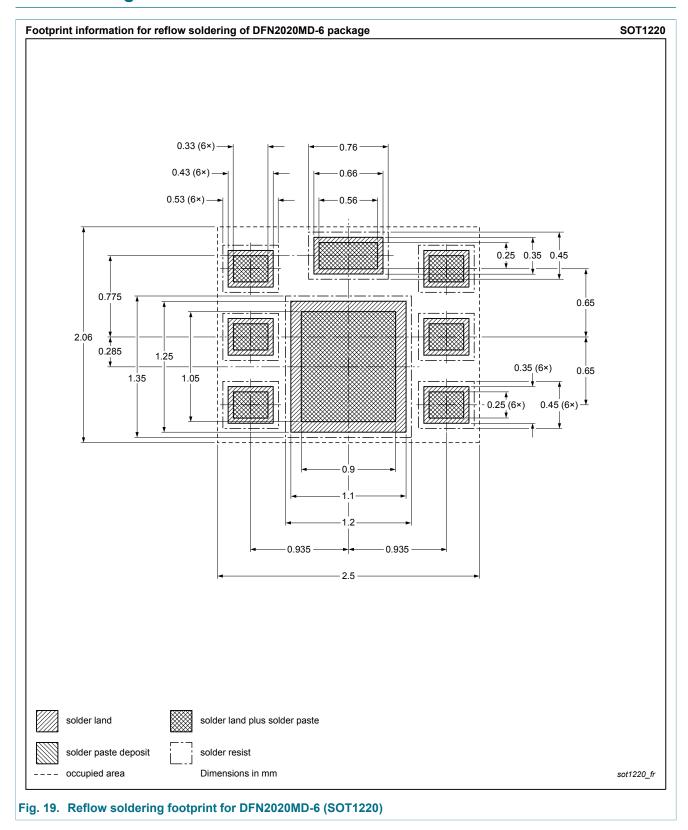
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PMPB85ENEA v.2	20131219	Product data sheet	-	PMPB85ENEA v.1			
Modifications:	 Products status chan 	Products status changed					
PMPB85ENEA v.1	20130219	Objective data sheet	-	-			

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15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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